MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

# TK58A06N1

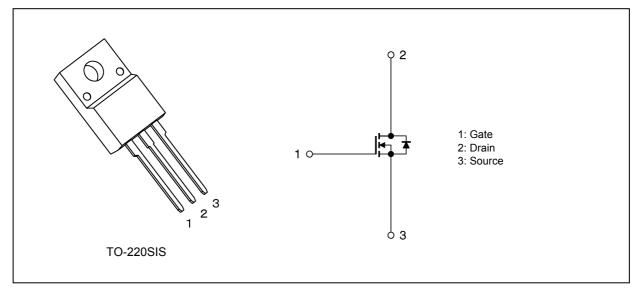
#### 1. Applications

• Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)}$  = 4.4 m $\Omega$  (typ.) (V<sub>GS</sub> = 10 V)
- (2) Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 60 \ V)$
- (3) Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V (V\_{DS} = 10 V,  $I_{D}$  = 0.5 mA)

#### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25°C unless otherwise specified)

Characte	Symbol	Rating	Unit		
Drain-source voltage			V <sub>DSS</sub>	60	V
Gate-source voltage			V <sub>GSS</sub>	±20	1
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	I <sub>D</sub>	105	A
Drain current (DC)	(T <sub>c</sub> = 25°C)	(Note 1)	Ι <sub>D</sub>	58	1
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I <sub>DP</sub>	269	1
Power dissipation	(T <sub>c</sub> = 25°C)		PD	35	W
Single-pulse avalanche energy		(Note 3)	E <sub>AS</sub>	158	mJ
Avalanche current			I <sub>AR</sub>	58	A
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	]

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	3.57	°C/W
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	62.5	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Limited by silicon chip capability. Package limit is 100A.

Note 3: V<sub>DD</sub> = 48 V, T<sub>ch</sub> = 25°C (initial), L = 36.1  $\mu$ H, I<sub>AR</sub> = 58 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

#### 6. Electrical Characteristics

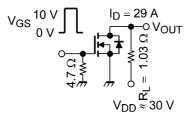
#### 6.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±20 V, $V_{DS}$ = 0 V	_	_	±0.1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V	-	—	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	60		_	V
Drain-source breakdown voltage (Note 4)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	45	_	_	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.5 mA	2.0	—	4.0	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 29 A	_	4.4	5.4	mΩ

Note 4: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

#### 6.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	3400		pF
Reverse transfer capacitance	C <sub>rss</sub>		_	45		
Output capacitance	C <sub>oss</sub>		_	1120	_	
Gate resistance	r <sub>g</sub>	—	_	2.6		Ω
Switching time (rise time)	tr	See Figure 6.2.1.	_	11		ns
Switching time (turn-on time)	t <sub>on</sub>		_	33		
Switching time (fall time)	t <sub>f</sub>		_	17	_	
Switching time (turn-off time)	t <sub>off</sub>		_	56	_	



 $Duty \le 1\%, \ t_w = 10 \ \mu s$  Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 48$ V, $V_{GS}$ = 10 V, $I_D$ = 58 A	—	46	—	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	15	_	
Gate-drain charge	Q <sub>gd</sub>		_	11	—	
Gate switch charge	Q <sub>SW</sub>			17		

#### 6.4. Source-Drain Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 5)	I <sub>DR</sub>	—	_	_	58	А
Reverse drain current (pulsed)	(Note 5)	I <sub>DRP</sub>	—	_		269	
Diode forward voltage		V <sub>DSF</sub>	I <sub>DR</sub> = 58 A, V <sub>GS</sub> = 0 V	_	_	-1.2	V
Reverse recovery time	(Note 6)	t <sub>rr</sub>	I <sub>DR</sub> = 58 A, V <sub>GS</sub> = 0 V		63		ns
Reverse recovery charge	(Note 6)	Q <sub>rr</sub>	-dI <sub>DR</sub> /dt = 100 A/µs	_	100	_	nC

Note 5: Ensure that the channel temperature does not exceed 150°C. Note 6: Ensure that  $V_{DS}$  peak does not exceed  $V_{DSS}$ .

#### 7. Marking (Note)

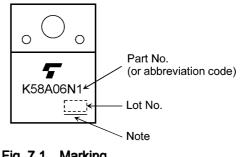


Fig. 7.1 Marking

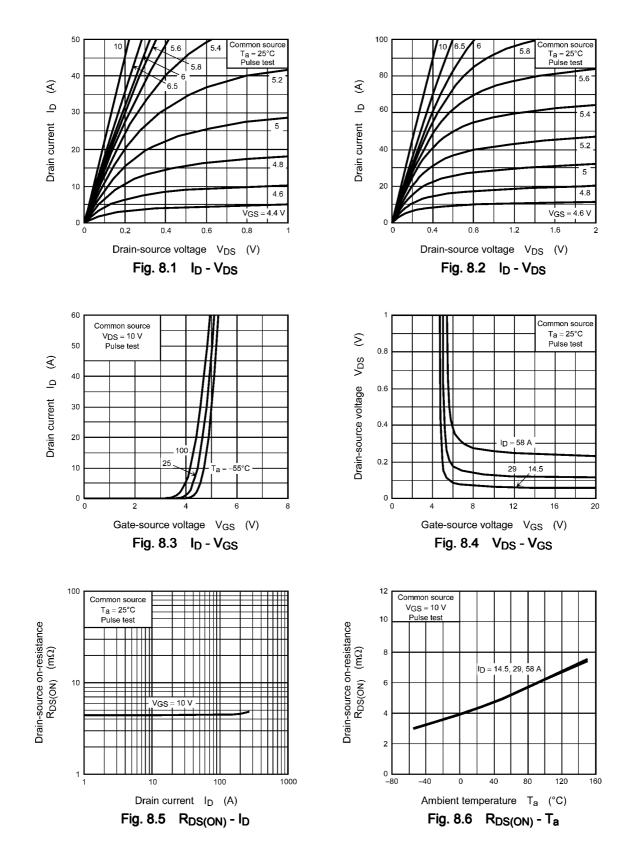
Note: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

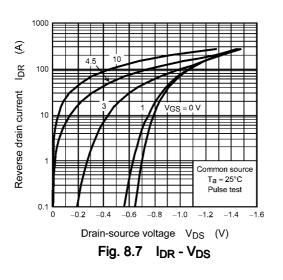
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

### 8. Characteristics Curves (Note)



5



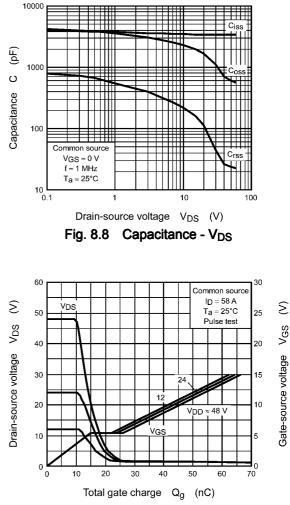
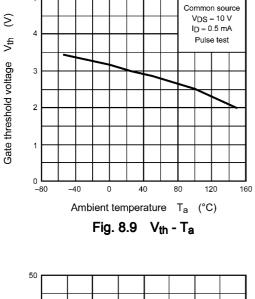
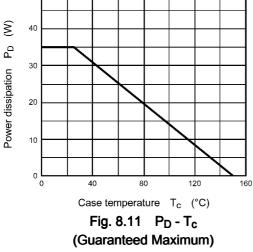
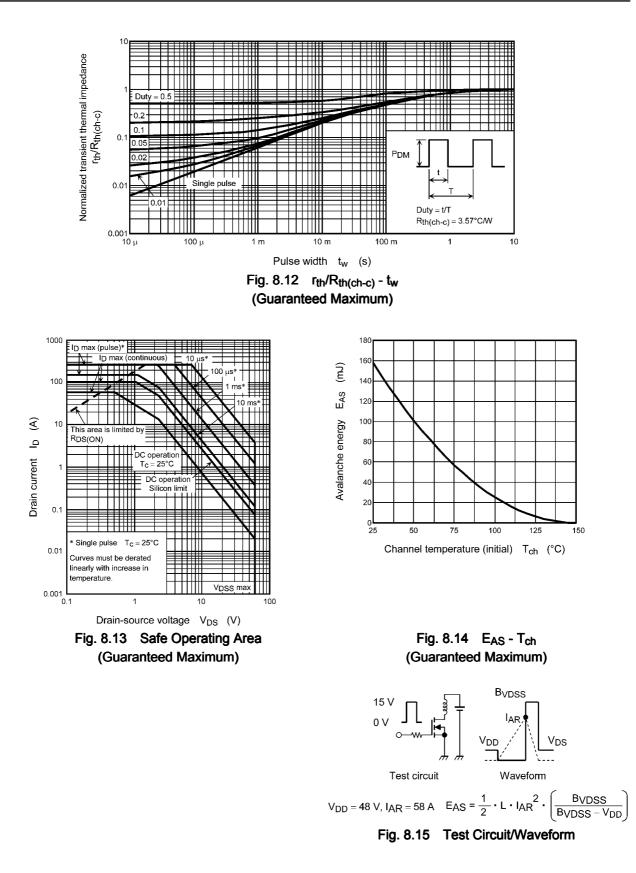


Fig. 8.10 Dynamic Input/Output Characteristics





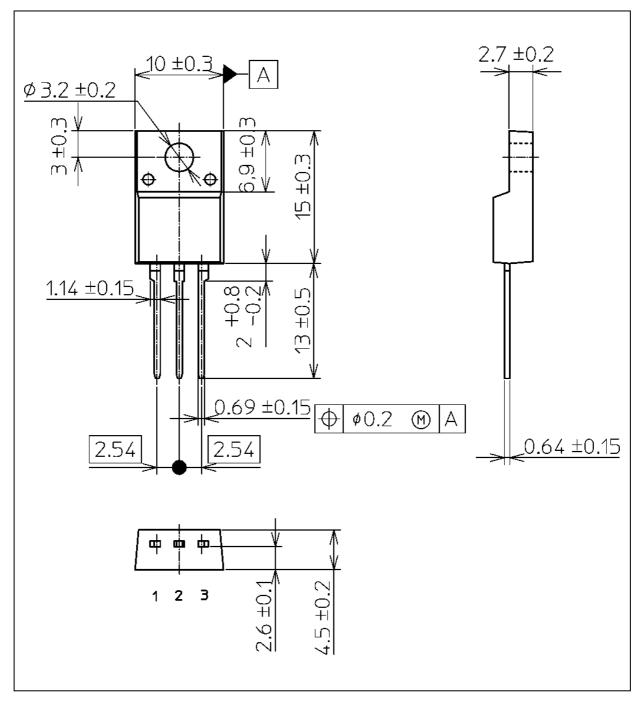


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

#### Package Dimensions

TK58A06N1

Unit: mm



Weight: 1.7 g (typ.)

Pac	ckage Name(s)
JEITA: SC-67	
TOSHIBA: 2-10U1S	
Nickname: TO-220SIS	

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